DEPARTMENT OF PHYSICS AND NANOTECHNOLOGY SRM INSTITUTE OF SCIENCE AND TECHNOLOGY SRM NAGAR, KATTANKULATHUR – 603 203

B.Tech – School of Computing- First Year/ First Semester

LESSON PLAN

SEMICONDUCTOR PHYSICS AND COMPUTATIONAL

Subject Name: METHODS Subject Code: 21PYB102J

	Module I				
Lectu	re Hour	Description	Reference		
S-1	SLO-1 SLO-2	Introduction to Classical Free electron theory Introduction to Quantum Free electron theory	Jasprit Singh, Semiconductor Devices (2001), Page 2-3		
S-2	SLO-1	Density of states – Concepts	Donald A. Neamen, 3 rd Edition, Semiconductor Physics and Devices, page 83- 85		
	SLO-2	Energy band in solids	S.M. Sze, Semiconductor Devices, 2 nd Edition, page 28- 30		
S-3	SLO-1	Kronig-Penney model	Donald A. Neamen, 3 rd Edition, Semiconductor		
3-3	SLO-2	Solving problems	Physics and Devices, Page 61-65		
S-4-5		Lab 1: Basics of experimentation	Lab		
S-6	SLO-1 SLO-2	Direct and Indirect band gap Concept of phonons-Concept of Brillouin Zone	S.M. Sze, Semiconductor Devices, page 30-32		
	SLO-1	E-k diagram – Basic concepts	S.M. Sze, Semiconductor Devices, page 30-32		
S-7	SLO-2	Concepts, Eigen value equations	Computational Materials Science: An Introduction by June Gunn Lee, Chapter 7, Page 227- 230 (Quantum Espresso) and Page 300 - 307 (VASP)		

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			And Chapter 4 page 108-120
S-8	SLO-1	Computational determination of Band Structure	http://physics.unl.edu/tsymbal/teaching/SSP- 927/Section%2011_Methods_f or_calculating_band_structure .pdf
			https://www.iue.tuwien.ac.at/p hd/ghosh/diss_htmse6.html
	SLO-2	Classification of electronic materials	S.M. Sze, Semiconductor Devices, page 32-33
S-9-10		Lab 2: Determination of Hall coefficient of Semiconductor material	Lab
	SLO-1	Fermi level	S.M. Sze, Semiconductor
S11	SLO-2	Probability of occupation	Devices, page 32-33
	SLO-1	Numerical determination of probability of occupation and carrier concentration	https://khitguntur.ac.in/shmat/ AP%20UNIT%20IV%20PPT
S-12	SLO-2	Concept of Fermi surface of a metal	%20II%20(Quantitative).pdf https://www.ias.ac.in/article/ful ltext/boms/045/0112 http://www- personal.umich.edu/~sunkai/te aching/Winter_2015/chapter08 .pdf
S-13	SLO-1	Computational determination of Fermi Surface of Cu as example	http://physics.unl.edu/tsymba l/teaching/SSP- 927/Section% 2011_Methods_ for_calculating_band_structu re.pdf https://iopscience.iop.org/arti cle/10.1088/1367- 2630/14/4/043009/pdf https://www.ias.ac.in/article/f ulltext/boms/045/0112 https://phy.ntnu.edu.tw/~cha ngmc/Teach/SS/SS_note/chap 09.pdf

	SLO-2	Bolving problems.	https://www.physics.udel.edu/~ msafrono/425- 2010/Lecture%208.pdf
S-14- 15		Lab 3: Determination of Band Gap of semiconductor-Post Office Box method	Lab

		Module II		
Lectu	re Hour	Description	Reference	
	SLO-1	Intrinsic semiconductor	S.M. Sze, Semiconductor Devices, page 34-36.	
S-1	SLO-2	Concept of carrier concentration, variation of Fermi level with temperature in intrinsic semiconductor	S.M. Sze, Semiconductor Devices, page 34-36.	
	SLO-1	Extrinsic semiconductors	Donald A. Neamen, 3 rd Edition, Semiconductor Physics and Devices, Page 139-144.	
S-2	SLO-2	Concepts of carrier concentration, variation of Fermi level with temperature in n and p type semiconductor	Donald A. Neamen, 3 rd Edition, Semiconductor Physics and Devices, Page 139-144.	
S-3	SLO-1	Explanation for carrier generation	S.M. Sze, Semiconductor Devices, page 60-66.	
	SLO-2	Solving problem	Devices, page 00-00.	
S - 4, 5	5	Lab 4: Determination of Band Gap of semiconductor-Four probe method	Lab	
	SLO-1	Diffusion and drift current	S.M. Sze, Semiconductor	
S-6	SLO-2	Continuity equation-p-n junction	Devices Physics and Technology, Second Edition, John Wiley & Sons, page 66-68.	
	SLO-1	Biasing concept in p-n junction	7.1.0	
S-7	SLO-2	Metal semiconductor junction	S.M. Sze, Semiconductor Devices, page 88-89.	
S-8	SLO-1	Ohmic contact	S.M. Sze, Semiconductor	

		Concepts of Carrier transport - diffusion and drift – Derivation of Continuity equation.	Devices, page 66-68.
	SLO-2 SLO-1 SLO-2	Lab 5: Study of I-V characteristics of a light dependent resistor (LDR)	Lab
	SLO-1	Semiconductor materials of interest for optoelectronic devices	S.M. Sze, Semiconductor Devices, page 88-89.
S-11	SLO-2 SLO-1	Photocurrent in a P-N junction diode Light emitting diode	Jasprit singh, page 463- 464 S.M. Sze, Semiconductor
S-12	SLO-2	Classification of Light emitting diode	Devices Physics and Technology, Second Edition, John Wiley & Sons, page 288-294.
	SLO-1	Optoelectronic integrated circuits	Jasprit singh, page 455
S-13	SLO-2	Organic light emitting diodes-Solving problem	Jasprit singh, page 463- 464
S-14- 15		Lab 6: Study of V-I and V-R characteristics, Efficiency of a solar cell	Lab

Module III				
Lecture Hour		Description	Reference	
S-1	SLO-1	Concepts of optical transition in bulk semiconductor	Saleh & Teich, Fundamentals of photonics,	
	SLO-2	Optical absorption process and emission process	Second edition, page 660-661.	
S-2	SLO-1	Concepts of Recombination process	P. Battacharya, page 116-118	
	SLO-2	Optical recombination process		
S-3	SLO-1	Explanation of spontaneous emission	P. Battacharya, page 244-245	
	SLO-2	Explanation of stimulated emission	3 / 1 8	

S-4-5		Lab 7: Characterization of pn junction diode	Lab
	SLO-1	Solving problem	Saleh & Teich,
S-6	SLO-2	Joint density of states (Conservation of energy and momenta of electron with photon interacts)	Fundamentals of photonics, Second edition, page 665.
	SLO-1	Density of states for photon	Shun Lien Chuang, Physics
S-7	SLO-2	Explanation of transition rates using Fermi's golden rule	of Photonic Devices, page 353-354
	SLO-1	Numerical computation of optical loss	https://nanohub.org/resource s/4883/download/tutorial_se miempirical_bandstructure methods.pdf
S-8	SLO-2	Finite element method to calculate Photon density of states	https://opg.optica.org/oe/fullt ext.cfm?uri=oe-15-1- 207&id=122646
S-9-10		Lab 8: Repeat/Revision of experiments	Lab
	SLO-1	Solving Problem	Chetan Singh Solanki, Solar
S-11	SLO-2	Basic concepts of Photovoltaic	Photovoltaics, 2rd Edition, page 89-94
	SLO-1	Photovoltaic effect, Applications of Photovoltaic effect	
S-12	SLO-2	Determination of efficiency of a PV cell	
	SLO-1	Computational approach to calculate optical excitations, Example: optical excitation in BN	https://www.nature.com/artic les/s41598-021-90804-4
S-13	SLO-2	Solving Problem	https://nanohub.org/resource s/4883/download/tutorial_se miempirical_bandstructure methods.pdf https://khitguntur.ac.in/shma t/AP%20UNIT%20IV%20P PT%20II%20(Quantitative).
S-14-		Lab 9: To verify Inverse square law of light	<u>pdf</u> https://www.ias.ac.in/article/f ulltext/boms/045/0112
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	Module IV				
Lectur	re Hour	Description	Reference		
S-1	SLO-1	Concepts of Electrical measurements	ELTON .N. KOUFMANN Characterization of Materials, Volume I		
5-1	SLO-2	Two point probe technique	1)ELTON .N. KOUFMANN Characterization of Materials, Volume I, Page 401		
	SLO-1	Four-point probe technique-linear method	ELTON .N. KOUFMANN		
S-2	SLO-2	Four-point probe technique-Van der Pauw method	Characterization of Materials, Volume I ,Page 404		
S-3	SLO-1 SLO-2	Significance of carrier density and Significance of resistivity and Hall mobility Solving problem	S.M. Sze, page 55-56		
	SLO-1	Lab 10: Determination of electron and hole			
S-4-5	SLO-2	mobility versus doping concentration using GNU Octave	Lab		
S-6	SLO-1	Hot-point probe measurement	FACTA UNIVERSITATIS Series: Electronics and Energetics Vol. 26, No 3, December 2013, pp. 187 - 195 DOI: 10.2298/FUEE1303187A		
	SLO-2	Capacitance-voltage measurements	ELTON .N. KOUFMANN Characterization of Materials, Volume I ,Page 456		
	SLO-1	Extraction of Parameters in a diode	ELTON .N. KOUFMANN		
S-7	SLO-2	I-V characteristics in a diode	Characterization of Materials, Volume I Page 466		
S-8	SLO-1	Introduction of TCAD in basic level	http://www.micro.deis.unibo.it /~rudan/MATERIALE_DIDA TTICO/diapositive/TCAD/01 TCAD_laboratory_Introducti on_GBB_20140303H1424.pdf		

			https://www.eng.auburn.edu/~ niuguof/elec6710dev/html/fun damental.html
	SLO-2	Solving problem	
S-9-10	SLO-1	Lab 11: Determination of Fermi function for different temperature using GNU Octave	Lab
S-11	SLO-1	Significance of band gap in semiconductors	Jaspirt singh, Semiconductor device, page 458-462
	SLO-2	Concept of absorption and emission	Jaspirt singh, Semiconductor device, page 458-462
	SLO-1	Boltzmann Transport Equation; Scattering Mechanisms	https://courses.physics.ucsd.ed u/2010/Winter/physics211b/L ECTURES/CH01.pdf
S-12	SLO-2	Monte Carlo method- Concept only	Computational Materials Science: An Introduction by June Gunn Lee, Chapter 7, Page 227- 230 (Quantum Espresso) and Page 300 - 307 (VASP) and page 6
_	SLO-1	Example only Monte Carlo Methods for Solution of BTE	Computational Materials Science: An Introduction by
S-13	SLO-2	Solving problem	June Gunn Lee, Chapter 7, Page 227- 230 (Quantum Espresso) and Page 300 - 307 (VASP) and Page 6
S-14- 15	SLO-1 SLO-2	Lab 12: Study of attenuation and propagation characteristic of optical fiber cable using laser source	Lab

Lectu	re Hour	Description	Reference
S-1	SLO-1	Density of states in 2D	Solid State Physics-Principles

	SLO-2	Density of states in 1D and 0D-Introduction to low dimensional systems	and Applications, by R. Asokmani, Page-220, Section- 7.3 & Section 7.5
S-2	SLO-1	Introduction to low dimensional systems	1)Physical Methods for material Characterization ,Ed 2,By-Flewitt and Wild, Ch- Physics of Low dimensional Semiconductors,Sec 7.3 to 7.5 (page 223) 2)Introduction to Nanotechnology , by Charles P.Poole,Jr.,Frank J.Owens
	SLO-2	Quantum well, Quantum wire, and dots	Introduction to Nanotechnology , by Charles P.Poole,Jr.,Frank J.Owens Ch-9,Section 9.3,3,9.3.5 and 9.3.6
S-3	SLO-1	Solving problems	Introduction to Nanotechnology , by Charles P.Poole,Jr.,Frank J.Owens
	SLO-2	CNT- properties and synthesis	Ch-9,Section 9.3,3,9.3.5 and 9.3.6
S-4-5	SLO-1 SLO-2	Lab 13: Plotting and interpretation of I-V characteristics of Diode GNU Octave	Lab
S-6	SLO-2	CNT- properties and synthesis Applications of CNTs	Nanotechnology VOl.1, By.W.M.Berck, First edition,Page 60 to 76
	SLO-1	Fabrication technique-CVD	Nanotechnology and Nanomaterials-Synthesis, Properties and Applications,By Guozhong Cao, Page189 -195,Section 5.5 to 5.5.4
S-7	SLO-2	Fabrication technique-PVD	Nanotechnology and Nanomaterials-Synthesis, Properties and Applications ,By Guozhong Cao, Page182 - 185,Section 5.4
S-8	SLO-1	Characterization techniques for low dimensional system	
	SLO-2	Solving problem	

S 09-10	SLO-1 SLO-2	Lab 14: Determination of lattice parameters using powder XRD	Lab
	SLO-1	Scanning electron microscopy	Material Characterization
S-11	SLO-2	Transmission electron microscopy	Techniques By Sam Zhang, Lin Li, Ashok Kumar,Page 177 to 190, Section 7.1.2 to 7.2.3
S-12	SLO-1	Transmission electron microscopy	Material Characterization Techniques By Sam Zhang, Lin Li, Ashok Kumar, Page 153, Section 6.1 to 6.3
	SLO-2	Atomic force microscope	Material Characterization Techniques By Sam Zhang, Lin Li, Ashok Kumar,Page 98, Section 4.2.2 to 4.4.2.3
S-13	SLO-1	Computational and machine learning approach for electron microscopy image processing Concepts, overview	https://www.sciencedirect.com /science/article/pii/S266638642 2002995
	SLO-2	Example of Graphene	https://www.sciencedirect.com /science/article/pii/S266638642 2002995
S 14-15	SLO-1 SLO-2	Mini Project	Lab

Course Coordinator

HOD/Physics and Nanotechnology

(Dr.T.Kalaivani)